

XG3029

N-Channel Enhancement Mode SGT MOSFET

30(VDS) / + 20 / - 16 (VGS) / 50A(ID)

Rev0.1

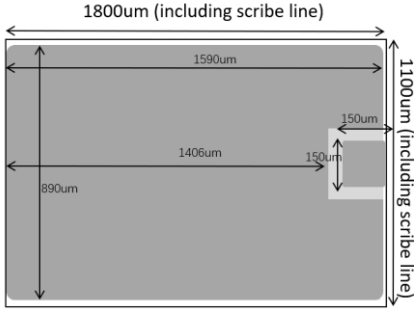


Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8,, wafer
XG3029	30(V _{DS}) / + 20/-16 V(V _{GS}) / 50A(I _D) N-Channel Enhancement Mode SGT MOSFET	14,500

2. Physical Characteristics

	Die Size:1800× 1100μm (including scribe line)
	Gate: 150μm × 150μm
	For PDFN5X6 package Suggest Bonding wire: Gate: 1*2.0 mil Cu Source: 16*2.0 mil Cu

3. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (1kÅ-3kÅ-8Å°)
Nominal Front Metal Composition, Thickness	ALCu (4m)
Wafer Diameter	200mm, with 010 notch
Wafer Thickness	125μm±10um
Scribe Line Width	60μm

4. Key Electrical Characteristics of Die (at T_J = 25 ° C, unless otherwise specified)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	-	-	V	V _{GS} =0V, I _D =250μA
I _{D(Device Ref)}	Continuous Drain Current	-	-	50	A	T _J =25°C
R _{DS(on)(FT)}	Static Drain-to-Source On-Resistance	-	4	5	mΩ	V _{GS} =10V, I _D =15A
V _{GS(th)}	Gate Threshold Voltage	1.2	1.8	2.5	V	V _{DS} =V _{GS} , I _D =250μA
I _{DSS}	Drain-to-Source Leakage Current	-	-	1	μA	V _{DS} =60V, V _{GS} =0V
I _{GSS}	Gate-to-Source Leakage Current	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 175°C Max				